

Features

- Uses PingWei advanced PerfectMOS4 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Qualified according to AEC-Q101 criteria

Benefits

- High robustness and reliability
- Increases maximum current capability
- Low power loss, high power density
- Solid design of source leadframe

Applications

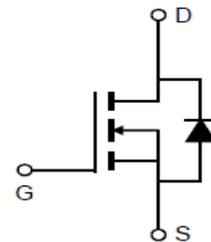
- Automotive applications
- Battery management
- Motor Drivers



100% DVDS Tested
100% Avalanche Tested

Product Summary

| | |
|-----------------------|-------|
| V_{DS} | 40V |
| $R_{DS(on)}@10V$ typ | 1.4mΩ |
| I_D (Silicon limit) | 185A |



Package Marking and Ordering Information

| Part # | Marking | Package | Packing | Reel Size | Tape Width | Qty |
|----------------|--------------|----------|-----------|-----------|------------|---------|
| PWC016N04UES4Q | C016N04UES4Q | UPDFN5x6 | Tape&Reel | 13 inches | 12mm | 5000pcs |

Absolute Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|----------------|------------|------------------|
| Drain-source voltage | V_{DS} | 40 | V |
| Continuous drain current | I_D | 185 | A |
| $T_C = 25^\circ\text{C}$ (Silicon limit) | | 131 | |
| $T_C = 100^\circ\text{C}$ (Silicon limit) | | 150 | |
| $T_C = 25^\circ\text{C}$ (Package limit) | | | |
| Pulsed drain current ($T_C = 25^\circ\text{C}$, $tp=100\mu\text{s}$) | $I_{D\ pulse}$ | 603 | A |
| Avalanche energy, single pulse ($L=0.1\text{mH}$, $V_{ds}=32\text{V}$) | E_{AS} | 145 | mJ |
| Avalanche energy, single pulse ($L=0.3\text{mH}$, $V_{ds}=32\text{V}$) | E_{AS} | 199 | mJ |
| Gate-Source voltage | V_{GS} | ± 20 | V |
| Power dissipation | P_{tot} | 97 | W |
| $T_C = 25^\circ\text{C}$ | | | |
| Operating junction and storage temperature | T_j, T_{stg} | -55...+175 | $^\circ\text{C}$ |
| Reflow soldering temperature (10s) | T_{sold} | 260 | $^\circ\text{C}$ |

Thermal Resistance

| Parameter | Symbol | Value | | | Unit | Test Condition |
|--|--------|-------|------|------|------|---|
| | | min. | typ. | max. | | |
| Thermal resistance, junction - case. | RthJC | - | - | 1.5 | °C/W | - |
| Thermal resistance, junction - ambient | RthJA | - | - | 59 | °C/W | 1 inch ² , 2oz single copper FR-4 PCB. |

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

| Parameter | Symbol | Value | | | Unit | Test Condition |
|-----------|--------|-------|------|------|------|----------------|
| | | min. | typ. | max. | | |

Static Characteristic

| | | | | | | |
|----------------------------------|---------------------|-----|-----|----------|----|--|
| Drain-source breakdown voltage | BV _{DSS} | 40 | - | - | V | V _{GS} =0V, I _D =250μA |
| Gate threshold voltage | V _{GS(th)} | 2.0 | 2.7 | 3.5 | V | V _{DS} =V _{GS} , I _D =250μA |
| Zero gate voltage drain current | I _{DSS} | - | - | 1 100 | μA | V _{DS} =40V, V _{GS} =0V T _j =25°C T _j =125°C |
| Gate-source leakage current | I _{GSS} | - | ±10 | ±100 | nA | V _{GS} =±20V, V _{DS} =0V |
| Drain-source on-state resistance | R _{DS(on)} | - | 1.4 | 1.6 | mΩ | V _{GS} =10V, I _D =50A |
| Transconductance | g _{fs} | - | 69 | - | S | V _{DS} =5V, I _D =50A |

Dynamic Characteristic

| | | | | | | |
|------------------------------|---------------------|---|------|------|----|--|
| Input Capacitance | C _{iss} | - | 2784 | 4176 | pF | V _{GS} =0V, V _{DS} =20V, f=100KHz |
| Output Capacitance | C _{oss} | - | 1366 | 2049 | | |
| Reverse Transfer Capacitance | C _{rss} | - | 33 | 66 | | |
| Gate Total Charge | Q _G | - | 37 | 56 | nC | V _{DS} =20V, I _D =50A, V _{GS} =10V |
| Gate-Source charge | Q _{gs} | - | 17 | 26 | | |
| Gate-Drain charge | Q _{gd} | - | 4 | 8 | | |
| Turn-on delay time | t _{d(on)} | - | 15 | - | ns | V _{GS} =10V, V _{DD} =20V, R _G =1.6Ω, I _D =50A |
| Rise time | t _r | - | 20 | - | | |
| Turn-off delay time | t _{d(off)} | - | 27 | - | | |
| Fall time | t _f | - | 6 | - | | |
| Gate resistance | R _G | - | 1.2 | - | Ω | V _{GS} =0V, V _{DS} =0V, f=1MHz |



Body Diode Characteristic

| Parameter | Symbol | Value | | | Unit | Test Condition |
|---------------------------------------|-------------|-------|------|------|------|---|
| | | min. | typ. | max. | | |
| Body Diode Forward Voltage | V_{SD} | - | - | 1.2 | V | $V_{GS}=0V, I_{SD}=50A$ |
| Body Diode Continuous Forward Current | I_S | - | - | 150 | A | TC = 25°C |
| Body Diode Pulsed Current | I_S pulse | - | - | 603 | A | TC = 25°C, $t_p=100\mu s$ |
| Body Diode Reverse Recovery Time | t_{rr} | - | 38 | - | ns | $V_R=20V, I_F=50A,$ $dI/dt=100A/\mu s$ |
| Body Diode Reverse Recovery Charge | Q_{rr} | - | 27 | - | nC | |

Typical Performance Characteristics

Fig 1: Output Characteristics

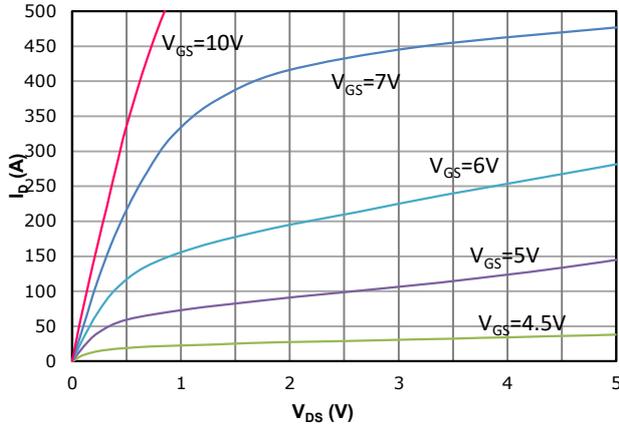


Fig 2: Transfer Characteristics

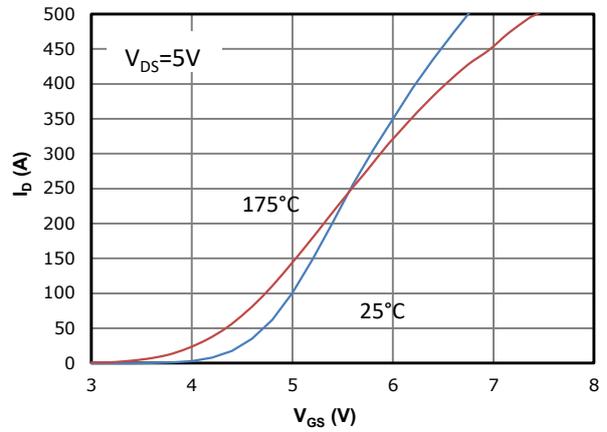


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

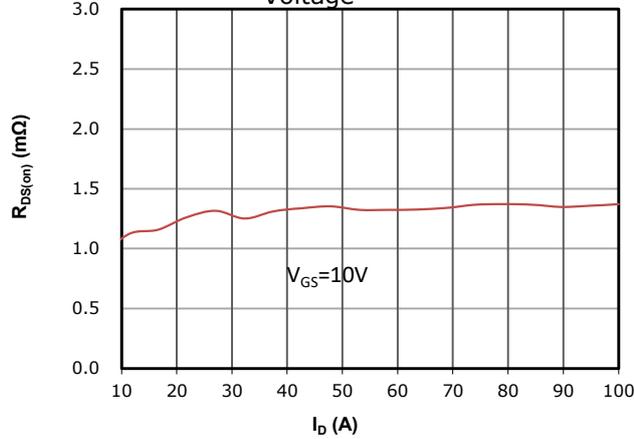


Fig 4: $R_{DS(on)}$ vs Gate Voltage

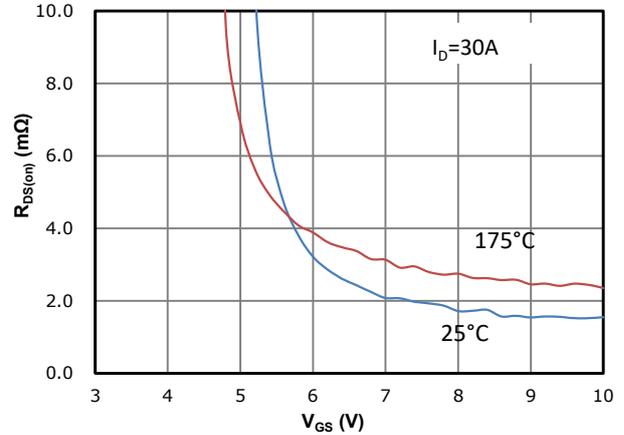


Fig 5: $R_{DS(on)}$ vs. Temperature

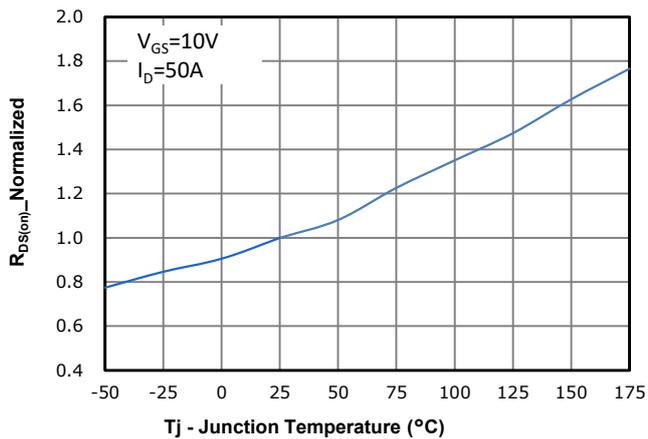


Fig 6: $V_{GS(th)}$ vs. Temperature

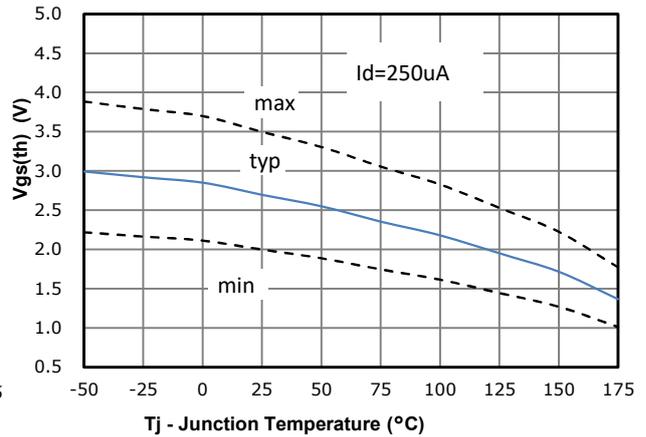


Fig 7: BVdss vs. Temperature

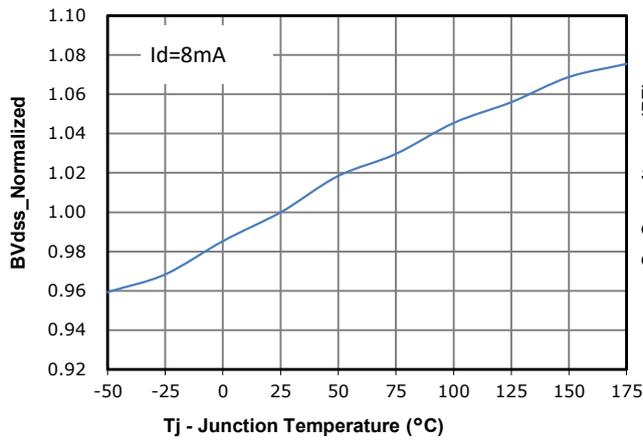


Fig 8: Capacitance Characteristics

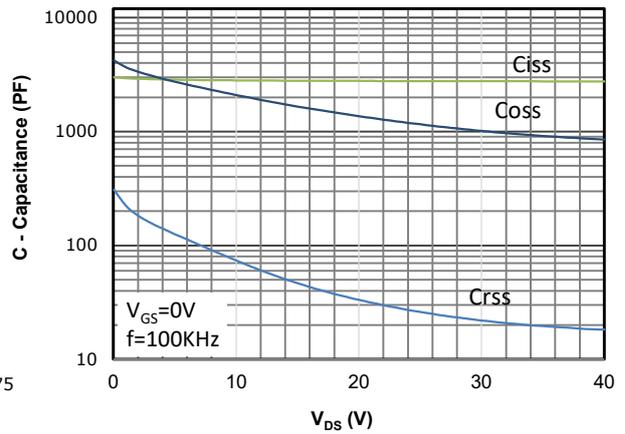


Fig 9: Gate Charge Characteristics

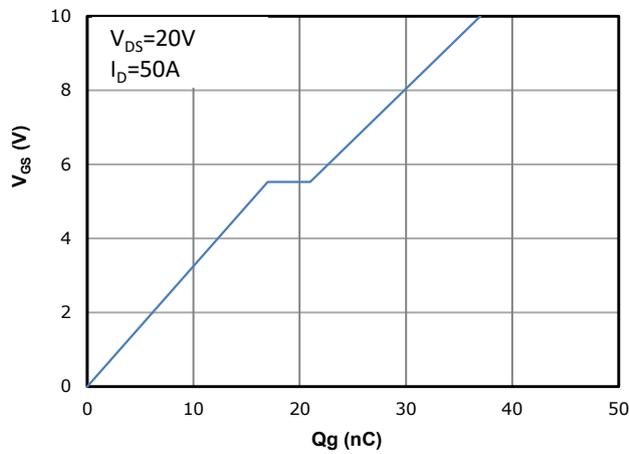


Fig 10: Body-diode Forward Characteristics

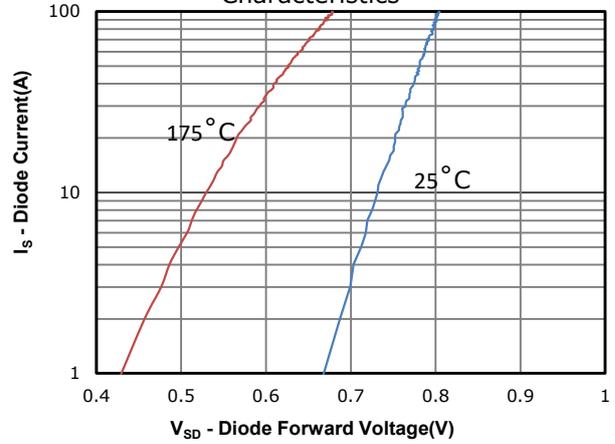


Fig 11: Power Dissipation

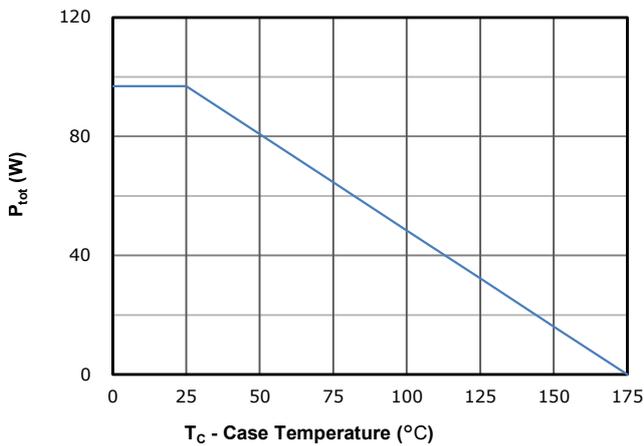


Fig 12: Drain Current Derating

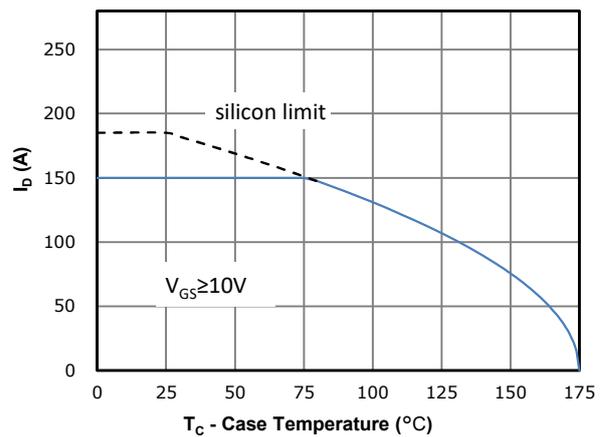


Fig 13: Safe Operating Area

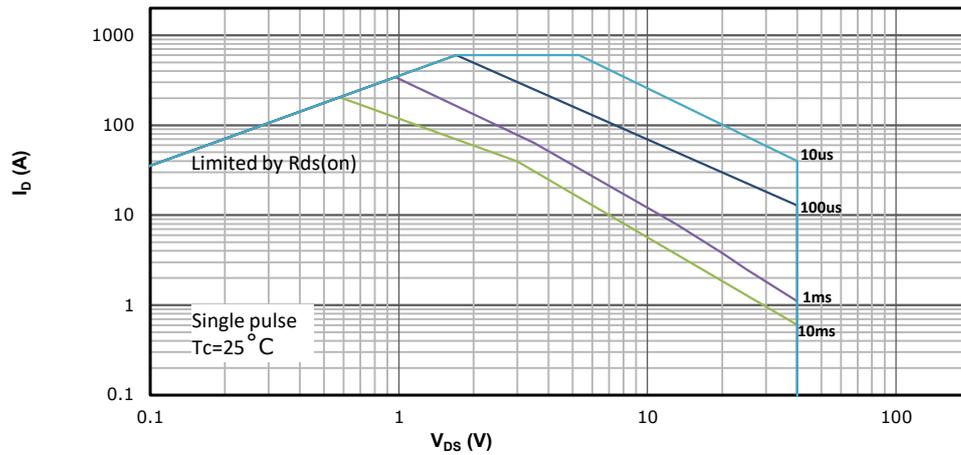
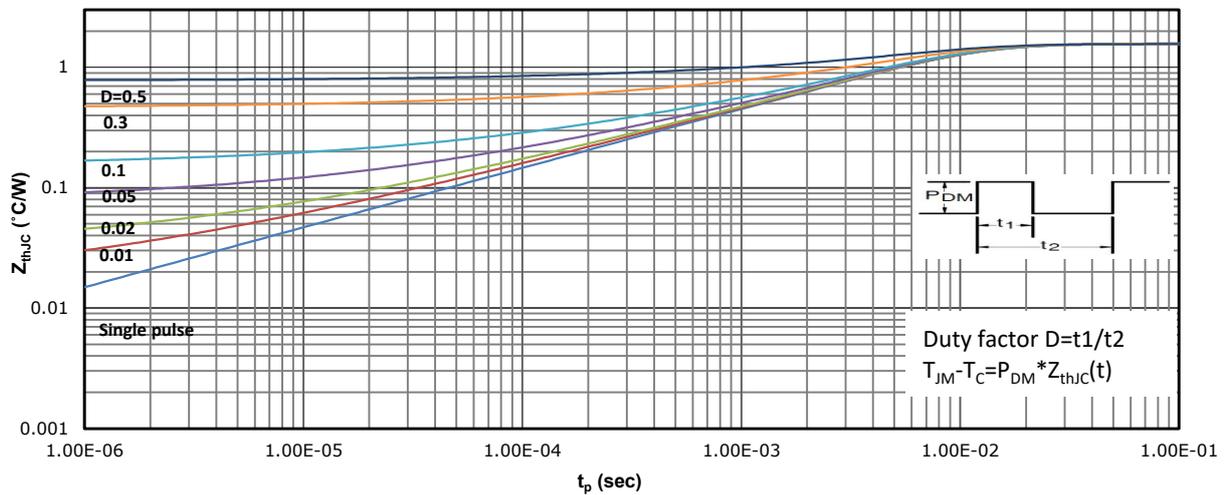
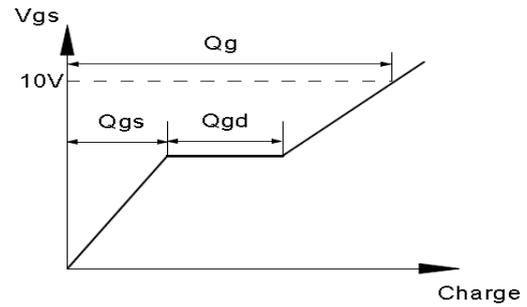
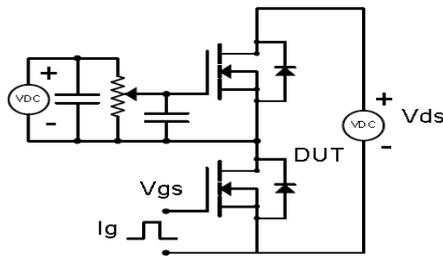


Fig 14: Max. Transient Thermal Impedance

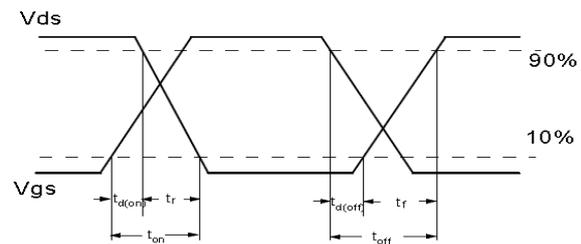
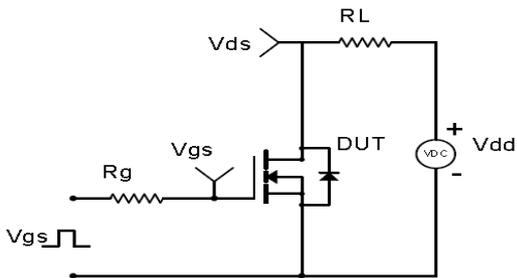


Test Circuit & Waveform

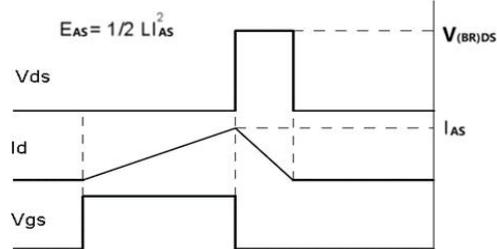
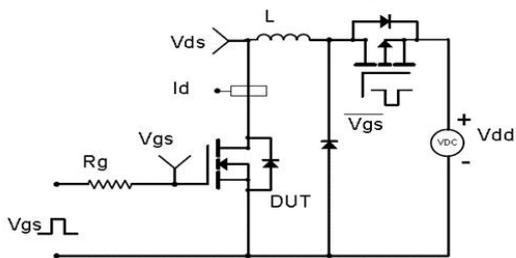
Gate Charge Test Circuit & Waveform



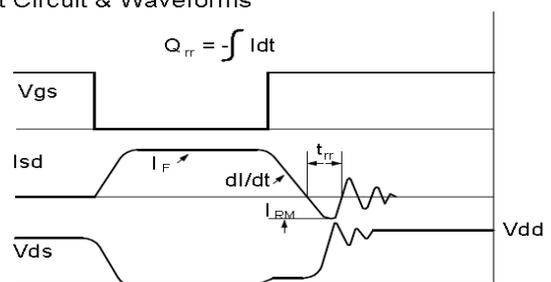
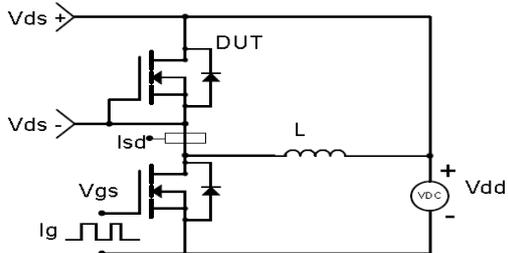
Resistive Switching Test Circuit & Waveforms



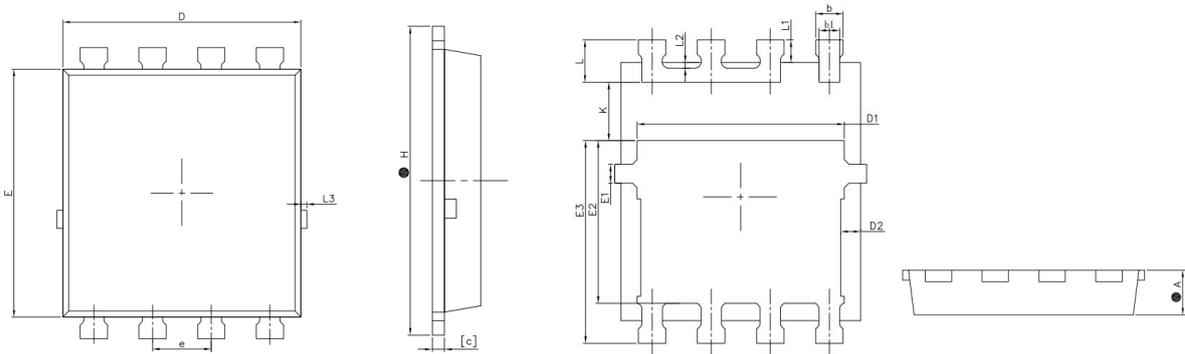
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: UPDFN5*6-C



| SYMBOL | MILLIMETERS | | INCHES | |
|--------|-------------|------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.90 | 1.10 | 0.035 | 0.043 |
| b | 0.49 | 0.69 | 0.019 | 0.027 |
| b1 | 0.34 | 0.54 | 0.013 | 0.021 |
| c | 0.20 | 0.30 | 0.008 | 0.012 |
| D | 4.95 | 5.35 | 0.195 | 0.211 |
| D1 | 4.45 | 4.85 | 0.175 | 0.191 |
| D2 | 0.23 | 0.63 | 0.009 | 0.025 |
| E | 5.28 | 5.68 | 0.208 | 0.224 |
| E1 | 0.25 | 0.60 | 0.010 | 0.024 |
| E2 | 3.20 | 3.70 | 0.126 | 0.146 |
| E3 | 4.05 | 4.55 | 0.159 | 0.179 |
| e | 1.27 | | 0.050 | |
| H | 6.19 | 6.69 | 0.244 | 0.263 |
| L | 0.65 | 1.15 | 0.026 | 0.045 |
| L1 | 0.28 | 0.68 | 0.011 | 0.027 |
| L2 | 0.12 | | 0.005 | |
| L3 | - | 0.23 | - | 0.009 |
| K | 1.04 | 1.44 | 0.041 | 0.057 |



Revision History

| Revision | Date | Major changes |
|----------|----------|----------------------------|
| 1.0 | 2026/2/7 | Release of Formal Version. |

Disclaimer

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

The product is not intended for use in applications that require extraordinary levels of quality and reliability, such as aviation/aerospace and life-support devices or systems.

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